

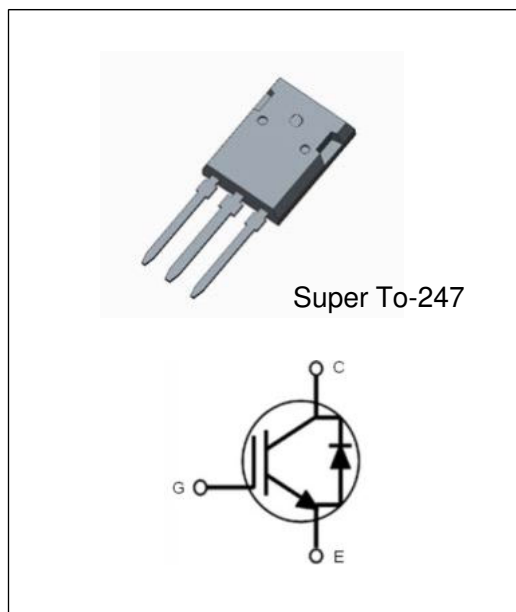
## 1200V 75A Field Stop Trench IGBT

### Description

The device is designed by advanced Field Stop Trench technology process. This IGBT offer low  $V_{CE(sat)}$ , high speed switching performance and excellent quality for application such as Welder, PV Inverter, Solar Inverter and other switching applications.

### Features

- Field Stop Trench Technology
- $V_{CE(sat)}=1.89V@I_C=75A$
- High Speed Switching & Low Power Loss
- High Input Impedance



### Applications

- UPS, Inverter, Welder, Solar Inverter

### Absolute Maximum Ratings

Symbol	Parameter	Ratings	Unit	
$V_{CES}$	Collector to Emitter Voltage	1200	V	
$V_{GES}$	Gate to Emitter Voltage	$\pm 20$	V	
$I_C$	Collector Current	$T_C=25^\circ C$	120	A
		$T_C=125^\circ C$	75	A
$I_{CM}$	Pulsed Collector Current	225	A	
$I_F$	Diode Continuous Forward Current	$T_C=125^\circ C$	50	A
$I_{FM}$	Diode Maximum Forward Current	250	A	
$P_D$	Maximum Power Dissipation	$T_C=25^\circ C$	830	W
		$T_C=125^\circ C$	415	W
$T_J$	Operating Junction Temperature Range	-40~+175	$^\circ C$	
$T_{STG}$	Storage Temperature Range	-50~+150	$^\circ C$	

### Thermal Characteristics

Symbol	Parameter	Ratings	Unit
$R_{th(J-C)}$ (IGBT)	Thermal Resistance, Junction to case for IGBT	0.18	$^\circ C/W$
$R_{th(J-C)}$ (Diode)	Thermal Resistance, Junction to case for Diode	0.78	$^\circ C/W$
$R_{th(J-A)}$	Thermal Resistance, Junction to Ambient	40	$^\circ C/W$

## Electrical Characteristics of IGBT @ $T_C=25\text{ }^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$BV_{CES}$	Collector to Emitter Breakdown Voltage	$V_{GE}=0V, I_C=250\mu A$	1200	-	-	V
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C=75A, V_{GE}=15V$	-	1.89	-	V
		$I_C=75A, V_{GE}=15V, T_C=125\text{ }^\circ\text{C}$	-	2.35	-	V
$V_{GE(th)}$	Gate Threshold Voltage	$V_{CE}=V_{GE}, I_C=250\mu A$	4.5	5.75	6.5	V
$I_{CES}$	Zero Gate Voltage Collector Current	$V_{CE}=V_{CES}, V_{GE}=0V$	-	-	1	mA
$I_{GES}$	Gate to Emitter Leakage Current	$V_{GE}=V_{GES}, V_{CE}=0V$	-	-	$\pm 250$	nA

## Electrical Characteristics of Diode @ $T_C=25\text{ }^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$V_F$	Diode Forward Voltage	$I_F=50A$	-	2.90	3.6	V
		$I_F=50A, T_C=125\text{ }^\circ\text{C}$	-	2.35	-	V
$t_{rr}$	Diode Reverse Recovery Time	$I_F=50A, di/dt=-220A/\mu s$	-	60	-	ns
$I_{rr}$	Diode Peak Reverse Recovery Current		-	9.5	-	A
$Q_{rr}$	Diode Reverse Recovery Charge		-	270	-	nC

## Switching Characteristics @ $T_C=25\text{ }^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit	
$t_{d(on)}$	Turn-on Delay Time	$I_C=75A, V_{CC}=600V, V_{GE}=15V, R_G=14\Omega$ Inductive Load, $T_C=25\text{ }^\circ\text{C}$	-	49.0	-	ns	
$t_r$	Rising Time		-	40.0	-	ns	
$t_{d(off)}$	Turn-off Delay Time		-	149	-	ns	
$t_f$	Falling Time		-	45.1	-	ns	
$E_{on}$	Turn-on Switching Loss		-	6.2	-	mJ	
$E_{off}$	Turn-off Switching Loss		-	3.6	-	mJ	
$E_{ts}$	Total Switching Loss		-	9.8	-	mJ	
$t_{d(on)}$	Turn-on Delay Time		$I_C=75A, V_{CC}=600V, V_{GE}=15V, R_G=14\Omega$ Inductive Load, $T_C=125\text{ }^\circ\text{C}$	-	46.6	-	ns
$t_r$	Rising Time			-	47.7	-	ns
$t_{d(off)}$	Turn-off Delay Time			-	162.5	-	ns
$t_f$	Falling Time	-		79.2	-	ns	
$E_{on}$	Turn-on Switching Loss	-		10.5	-	mJ	
$E_{off}$	Turn-off Switching Loss	-		6.2	-	mJ	
$E_{ts}$	Total Switching Loss	-		16.7	-	mJ	
$C_{ies}$	Input Capacitance	$V_{GE}=0V, V_{CE}=30V, f=1.0MHz$	-	6023	-	pF	
$C_{res}$	Reverse Transfer Capacitance		-	57	-	pF	
$C_{oes}$	Output Capacitance		-	446	-	pF	
$Q_g$	Total Gate Charge	$I_C=75A, V_{CC}=600V, V_{GE}=15V$	-	261	-	nC	
$Q_{ge}$	Gate to Emitter Charge		-	33	-	nC	
$Q_{gc}$	Gate to Collector Charge		-	157	-	nC	
$t_{sc}$	Short Circuit Withstand Time	$V_{CC}=600V, V_{GE}=15V$	6	-	-	us	

**Typical Performance Characteristics**

Fig. 1. Typical Output Characteristics

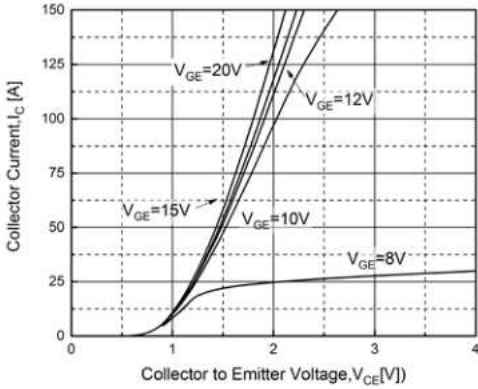


Fig. 2. Typical Saturation Voltage Characteristics

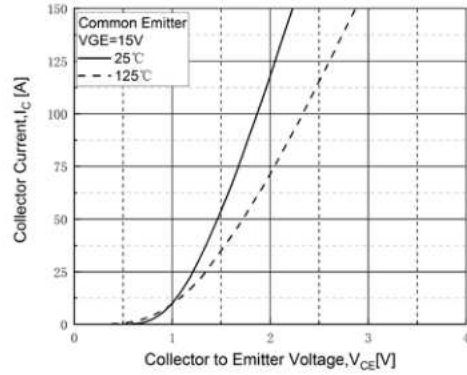


Fig. 3. Typical Saturation Voltage vs.  $T_C$

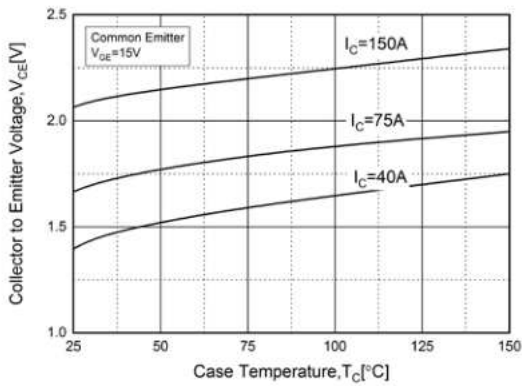


Fig. 4. Diode Forward Characteristics

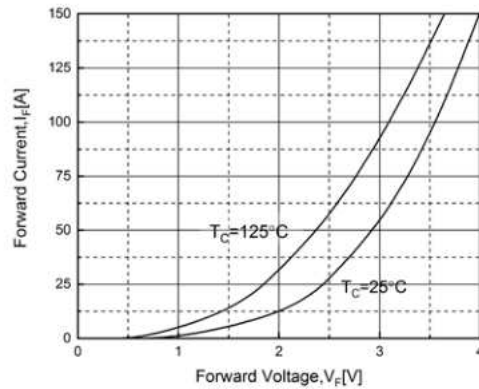


Fig. 5. Typical Capacitance Characteristics

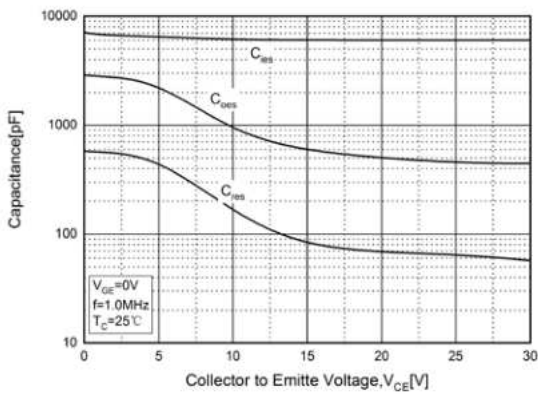
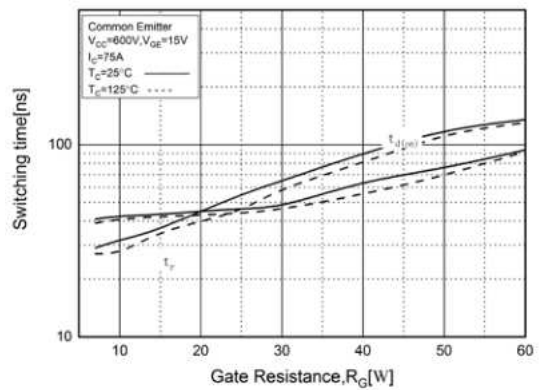


Fig. 6. Turn-on Characteristics vs.  $R_G$



**Typical Performance Characteristics**

Fig. 7. Turn-off Characteristics vs.  $R_G$

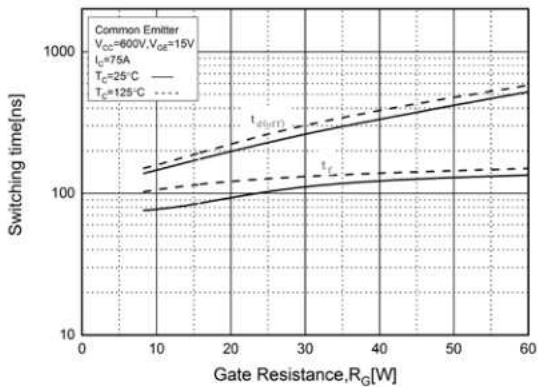


Fig. 8. Switching Loss vs.  $R_G$

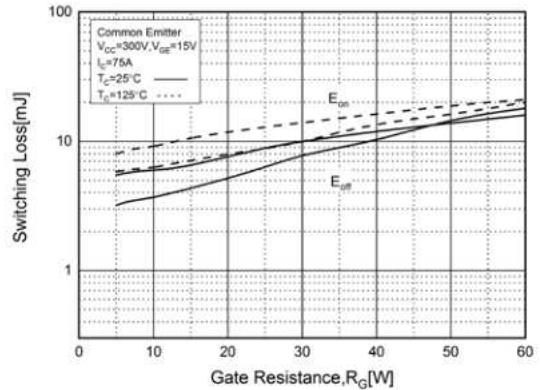


Fig. 9. Turn-on Characteristics vs.  $I_C$

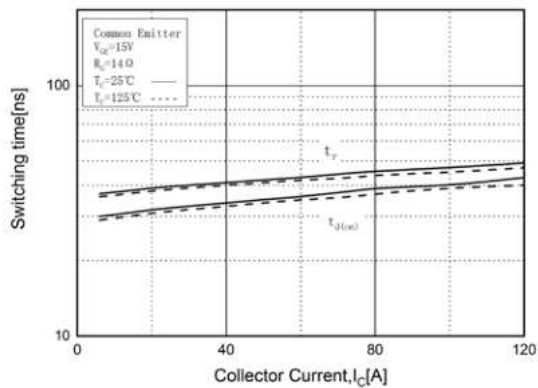


Fig. 10. Turn-off Characteristics vs.  $I_C$

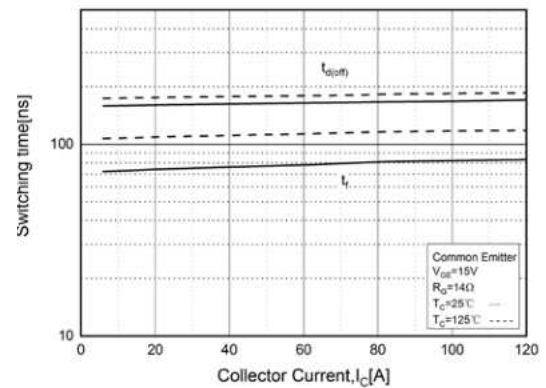
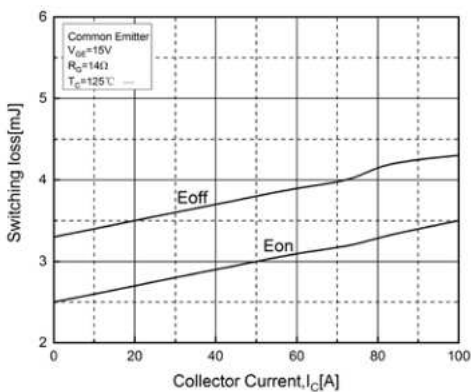


Fig. 11. Switching Loss vs.  $I_C$



**Package Dimensions**

**TO-247-Super**

(Dimensions in Millimeters)

